



PMV22EN

30 V, 5.2 A N-channel Trench MOSFET

Rev. 1 — 30 March 2011

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Very fast switching

1.3 Applications

- Relay driver
- Low-side loadswitch
- High-speed line driver
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25\text{ °C}$	-	-	30	V
V_{GS}	gate-source voltage		-20	-	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	5.2	A
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 5.2\text{ A};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.01; T_j = 25\text{ °C}$	-	17	22	mΩ

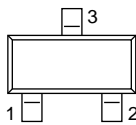
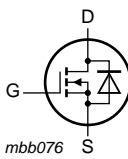
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 SOT23 (TO-236AB)	 mbb076
2	S	source		
3	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV22EN	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25\text{ °C}$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ °C}$	[1]	5.2	A
		$V_{GS} = 10\text{ V}; T_{amb} = 100\text{ °C}$	[1]	3.3	A
I_{DM}	peak drain current	$T_{amb} = 25\text{ °C};$ single pulse; $t_p \leq 10\text{ }\mu\text{s}$	-	20	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	510	mW
			[1]	930	mW
		$T_{sp} = 25\text{ °C}$	-	4170	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-55	150	°C
T_{stg}	storage temperature		-65	150	°C
Source-drain diode					
I_S	source current	$T_{amb} = 25\text{ °C}$	[1]	930	mA

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	207	245	K/W
			[2]	-	116	135	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	20	30	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ }^\circ C$	1	1.5	2.5	V
I_{DSS}	drain leakage current	$V_{DS} = 30 V$; $V_{GS} = 0 V$; $T_{amb} = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 30 V$; $V_{GS} = 0 V$; $T_{amb} = 150 \text{ }^\circ C$	-	-	10	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -20 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 V$; $I_D = 5.2 A$; pulsed; $t_p \leq 300 \mu s$; $\delta \leq 0.01$; $T_j = 25 \text{ }^\circ C$	-	17	22	m Ω
		$V_{GS} = 10 V$; $I_D = 5.2 A$; pulsed; $t_p \leq 300 \mu s$; $\delta \leq 0.01$; $T_j = 150 \text{ }^\circ C$	-	27	34	m Ω
		$V_{GS} = 4.5 V$; $I_D = 4.5 A$; pulsed; $t_p \leq 300 \mu s$; $\delta \leq 0.01$; $T_j = 25 \text{ }^\circ C$	-	22	29	m Ω
g_{fs}	forward transconductance	$V_{DS} = 5 V$; $I_D = 3 A$; pulsed; $t_p \leq 300 \mu s$; $\delta \leq 0.01$; $T_j = 25 \text{ }^\circ C$	-	12	-	S
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 3 A$; $V_{DS} = 15 V$; $V_{GS} = 10 V$; $T_j = 25 \text{ }^\circ C$	-	8.6	13	nC
Q_{GS}	gate-source charge		-	1.2	-	nC
Q_{GD}	gate-drain charge		-	1.3	-	nC
C_{iss}	input capacitance	$V_{GS} = 0 V$; $V_{DS} = 15 V$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ C$	-	480	-	pF
C_{oss}	output capacitance		-	110	-	pF
C_{rss}	reverse transfer capacitance		-	52	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 V$; $V_{GS} = 10 V$; $R_{G(ext)} = 6 \Omega$; $T_j = 25 \text{ }^\circ C$; $I_D = 3 A$	-	4	-	ns
t_r	rise time		-	15	-	ns
$t_{d(off)}$	turn-off delay time		-	100	-	ns
t_f	fall time		-	40	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 0.93 A$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	0.72	1.2	V